

# Hiroyuki Yaguchi

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

186  
papers

2,425  
citations

23  
h-index

40  
g-index

212  
ext. papers

2,559  
ext. citations

1.8  
avg, IF

4.23  
L-index

#	Paper	IF	Citations
186	Insights into Microscopic Crystal Growth Dynamics of CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> under a Laser Deposition Process Revealed by X-ray Diffraction. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 22559-22566	9.5	0
185	Enhanced Strain Relaxation in AlGa <sub>N</sub> Layers Grown on Sputter-Based AlN Templates. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900590	1.3	0
184	Epitaxial growth of CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> on rubrene single crystal. <i>APL Materials</i> , <b>2020</b> , 8, 041104	5.7	4
183	Spectral Change of E <sub>1</sub> Band Emission in a GaAs:N Doped Superlattice Due to Below-Gap Excitation and Its Discrimination from Thermal Activation. <i>Journal of Electronic Materials</i> , <b>2020</b> , 49, 1550-1556	1.0	1
182	Detection of Nonradiative Recombination Centers in GaPN (N:0.105%) by Below-Gap Excitation Light. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900377	1.3	2
181	Photoluminescence intensity change of GaP <sub>1-x</sub> N <sub>x</sub> alloys by laser irradiation. <i>AIP Advances</i> , <b>2020</b> , 10, 095302	1.5	0
180	Evolution of morphology and crystalline quality of DC-sputtered AlN films with high-temperature annealing. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SC1029	1.4	6
179	Photoluminescence characterization of nonradiative recombination centers in MOVPE grown GaAs:N Doped superlattice structure. <i>Optical Materials</i> , <b>2019</b> , 89, 521-527	3.3	1
178	Growth temperature dependence of cubic GaN step structures and cubic InN dot arrays grown on MgO (001) vicinal substrates. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SC1051	1.4	2
177	Biexciton Emission From Single Quantum-Confined Structures in N-Polar (000-1) InGa <sub>N</sub> /Ga <sub>N</sub> Multiple Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700454	1.3	
176	Nonradiative recombination centers in GaAs:N Doped superlattice revealed by two-wavelength-excited photoluminescence. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 161426	2.5	3
175	Effects of solvent vapor annealing on organic photovoltaics with a new type of solution-processable oligothiophene-based electronic donor material. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 08RE09	1.4	3
174	Photoluminescence Characterization of Carrier Recombination Centers in 4H-SiC Substrates by Utilizing below Gap Excitation. <i>Materials Science Forum</i> , <b>2017</b> , 897, 315-318	0.4	
173	Growth of InN/GaN dots on 4H-SiC(0001) $\omega$ vicinal substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2017</b> , 477, 201-206	1.6	4
172	Self-organized growth of cubic InN dot arrays on cubic GaN using MgO (001) vicinal substrates. <i>Physica Status Solidi (B): Basic Research</i> , <b>2017</b> , 254, 1600542	1.3	5
171	Spectral change of intermediate band luminescence in GaP:N due to below-gap excitation: Discrimination from thermal activation. <i>Physica Status Solidi (B): Basic Research</i> , <b>2017</b> , 254, 1600566	1.3	6
170	Photoluminescence Study of Oxidation-Induced Stacking Faults in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2015</b> , 821-823, 327-330	0.4	1

169	Growth temperature dependence of the surface segregation of Er atoms in GaAs during molecular beam epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 051201	1.4	
168	Differences in SiC thermal oxidation process between crystalline surface orientations observed by in-situ spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 095306	2.5	29
167	Control of intermediate-band configuration in GaAs:N $\delta$ -doped superlattice. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 08KA04	1.4	5
166	Surface Orientation Dependence of SiC Oxidation Process Studied by In Situ Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , <b>2015</b> , 821-823, 371-374	0.4	1
165	Photoluminescence study of oxidation-induced faults in 4H-SiC epilayers. <i>AIP Advances</i> , <b>2015</b> , 5, 127116	1.5	6
164	Molecular beam epitaxial growth of intermediate-band materials based on GaAs:N $\delta$ -doped superlattices. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 08KA07	1.4	4
163	Microstructures of InN film on 4H-SiC (0001) substrate grown by RF-MBE. <i>Journal of Semiconductors</i> , <b>2015</b> , 36, 083002	2.3	6
162	First-principles study on the conduction band electron states of GaAsN alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 911-913		3
161	Enhanced optical absorption due to E <sup>+</sup> -related band transition in GaAs:N $\delta$ -doped superlattices. <i>Applied Physics Express</i> , <b>2014</b> , 7, 102301	2.4	8
160	Photoreflectance study of the temperature dependence of excitonic transitions in dilute GaAsN alloys. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 752-755	1.6	4
159	Si Emission into the Oxide Layer during Oxidation of Silicon Carbide. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 553-556	0.4	3
158	Molecular beam epitaxy of ErGaAs alloys on GaAs (0 0 1) substrates. <i>Journal of Crystal Growth</i> , <b>2013</b> , 378, 85-87	1.6	1
157	Analysis of Electronic Structures of Nitrogen $\delta$ -Doped GaAs Superlattices for High Efficiency Intermediate Band Solar Cells. <i>IEEE Journal of Photovoltaics</i> , <b>2013</b> , 3, 1287-1291	3.7	6
156	RF-MBE growth of cubic AlN on MgO (001) substrates via 2-step c-GaN buffer layer. <i>Journal of Crystal Growth</i> , <b>2013</b> , 378, 307-309	1.6	4
155	RF-MBE growth of cubic InN nano-scale dots on cubic GaN. <i>Journal of Crystal Growth</i> , <b>2013</b> , 378, 454-458	1.6	5
154	Model Calculations of SiC Oxide Growth Rates at Sub-Atmospheric Pressures Using the Si and C Emission Model. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 833-836	0.4	3
153	Stacked structure of self-organized cubic InN nano-dots grown by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 1545-1548		3
152	Observation of optical spin injection into Ge-based structures at room temperature. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 242104	3.4	4

151	Conversion Efficiency of Intermediate Band Solar Cells with GaAs:N EDoped Superlattices. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 102302	1.4	6
150	OPTICAL PROPERTIES AND CARRIER DYNAMICS IN ASYMMETRIC COUPLED InGaN MULTIPLE QUANTUM WELLS. <i>Functional Materials Letters</i> , <b>2013</b> , 06, 1350021	1.2	5
149	Direct Evidence of Carrier Excitation from Intermediate Band States in GaPN by Two-Wavelength Excited Photoluminescence. <i>Applied Physics Express</i> , <b>2013</b> , 6, 092401	2.4	7
148	Oxygen partial pressure dependence of the SiC oxidation process studied by in-situ spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 024502	2.5	21
147	Influence of off-cut angle of (0001) 4H-SiC on the crystal quality of InN grown by RF-MBE. <i>Procedia Engineering</i> , <b>2012</b> , 32, 882-887		5
146	Thermal Oxidation Mechanism of Silicon Carbide <b>2012</b> ,		6
145	Nondestructive and Contactless Characterization Method for Spatial Mapping of the Thickness and Electrical Properties in Homo-Epitaxially Grown SiC Epilayers Using Infrared Reflectance Spectroscopy <b>2012</b> ,		2
144	RF-MBE growth of semipolar InN(10-13) and InGaN(10-13) on GaAs(110). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 658-661		2
143	Single Photon Generation from Nitrogen Atomic-Layer Doped Gallium Arsenide. <i>Materials Science Forum</i> , <b>2012</b> , 706-709, 2916-2921	0.4	2
142	TEM Analysis of Structural Phase Transition in MBE Grown Cubic InN on MgO (001) by MBE: Effect of Hexagonal Phase Inclusion in a C-Gan Nucleation Layer. <i>Applied Mechanics and Materials</i> , <b>2012</b> , 229-231, 219-222	0.3	
141	Biexciton Luminescence from Individual Isoelectronic Traps in Nitrogen $\delta$ -Doped GaAs. <i>Applied Physics Express</i> , <b>2012</b> , 5, 111201	2.4	8
140	Micro-Photoluminescence Study on the Influence of Oxidation on Stacking Faults in 4H-SiC Epilayers. <i>Applied Physics Express</i> , <b>2012</b> , 5, 051302	2.4	2
139	High Cubic-Phase Purity InN on MgO (001) Using Cubic-Phase GaN as a Buffer Layer <b>2011</b> ,		3
138	Single photon emission from nitrogen delta-doped semiconductors <b>2011</b> ,		3
137	Quantum well double barrier resonant tunneling structures for selective contacts of hot carrier solar cells <b>2011</b> ,		6
136	Theoretical Studies for Si and C Emission into SiC Layer during Oxidation. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 429-432	0.4	9
135	Model Calculations of SiC Oxide Growth Rate at Various Oxidation Temperatures Based on the Silicon and Carbon Emission Model. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 809-812	0.4	5
134	In Situ Spectroscopic Ellipsometry Study of SiC Oxidation at Low Oxygen-Partial-Pressures. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 813-816	0.4	2

133	Photoluminescence from single isoelectronic traps in nitrogen delta-doped GaAs grown on GaAs(111)A. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 2529-2531	3	12
132	RF-MBE growth of InN on 4H-SiC (0001) with off-angles. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 2016-2018		2
131	Model Calculation of SiC Oxide Growth Rate Based on the Silicon and Carbon Emission Model. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 489-492	0.4	6
130	Observation of SiC Oxidation in Ultra-Thin Oxide Regime by In Situ Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 509-512	0.4	2
129	Characterization of 4H-SiC/BiO <sub>2</sub> Interfaces by a Deep Ultraviolet Spectroscopic Ellipsometer. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 505-508	0.4	8
128	Optical and electrical characterizations of 4H-SiC/oxide interfaces by spectroscopic ellipsometry and capacitance-voltage measurements. <i>Applied Surface Science</i> , <b>2009</b> , 255, 8648-8653	6.7	13
127	A Kinetic Model of Silicon Carbide Oxidation Based on the Interfacial Silicon and Carbon Emission Phenomenon. <i>Applied Physics Express</i> , <b>2009</b> , 2, 021203	2.4	64
126	Model Calculation of SiC Oxidation Rates in the Thin Oxide Regime. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 663-666	0.4	7
125	Oxygen-Partial-Pressure Dependence of SiC Oxidation Rate Studied by In Situ Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 667-670	0.4	8
124	High Resolution X-Ray Diffraction and Raman Scattering Studies of Cubic-Phase InN Films Grown by MBE. <i>Advanced Materials Research</i> , <b>2008</b> , 55-57, 773-776	0.5	1
123	Oxide Growth Rate Enhancement of Silicon Carbide (0001) Si-Faces in Thin Oxide Regime. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7803-7806	1.4	39
122	Photoluminescence of cubic InN films on MgO (001) substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1579-1581		11
121	Photoluminescence study of hexagonal InN/InGaN quantum well structures grown on 3C-SiC (001) substrates by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1730-1732		1
120	Improvement of the surface morphology of a-plane InN using low-temperature InN buffer layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1808-1810		10
119	Twin photoluminescence peaks from single isoelectronic traps in nitrogen doped GaAs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 2110-2112	3	16
118	Micro-Raman study on the improvement of luminescence efficiency of GaAsN alloys. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 131-134	1.6	2
117	Micro-photoluminescence study of nitrogen delta-doped GaAs grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 73-75	1.6	11
116	RF-MBE growth of a-plane InN on r-plane sapphire with a GaN underlayer. <i>Journal of Crystal Growth</i> , <b>2007</b> , 301-302, 517-520	1.6	18

115	RF-MBE growth of InN/InGaN quantum well structures on 3C-SiC substrates. <i>Journal of Crystal Growth</i> , <b>2007</b> , 301-302, 513-516	1.6	7
114	Photoluminescence study of isoelectronic traps in dilute GaAsN alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2007</b> , 4, 2760-2763		5
113	Structural and optical characterization of high In content cubic InGaN on GaAs(001) substrates by RF-MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2007</b> , 4, 2437-2440		2
112	Growth Rate Enhancement of (000bar1)-Face Silicon Carbide Oxidation in Thin Oxide Regime. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L770-L772	1.4	29
111	Modulation spectroscopic investigation on lattice polarity of gallium nitride. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 061917	3.4	10
110	Simultaneous Determination of the Carrier Concentration, Mobility and Thickness of SiC Homo-Epilayers Using Terahertz Reflectance Spectroscopy. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 423-426	0.4	1
109	Characterization of oxide films on 4H-SiC epitaxial (0001) faces by high-energy-resolution photoemission spectroscopy: Comparison between wet and dry oxidation. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 053710	2.5	18
108	Off-Angle Dependence of Characteristics of 4H-SiC-Oxide Interfaces. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 1003-1006	0.4	3
107	Real Time Observation of SiC Oxidation Using an In Situ Ellipsometer. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 1031-1034	0.4	12
106	Simultaneous Determination of Carrier Concentration, Mobility, and Thickness of SiC Homoepilayers by Infrared Reflectance Spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L1226-L1229	1.4	15
105	RF-MBE growth of cubic InN films on MgO (001) substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 1515-1518		17
104	Photo-induced improvement of radiative efficiency and structural changes in GaAsN alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 1907-1910		2
103	Growth of high-quality hexagonal InN on 3C-SiC (001) by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 2267-2270		10
102	Characterization of Oxide Films on SiC Epitaxial (000-1) Faces by Angle-Resolved Photoemission Spectroscopy Measurements Using Synchrotron Radiation. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 585-588	0.4	3
101	Effect of Ar post-oxidation annealing on oxide/SiC interfaces studied by capacitance to voltage measurements and photoemission spectroscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2005</b> , 23, 298-303	2.9	19
100	Characterization of Electrical Properties in High-Dose Implanted and Post-Implantation-Annealed 4H-SiC Wafers using Infrared Reflectance Spectroscopy. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 905-908	0.4	4
99	Photoemission Spectroscopic Studies on Oxide/SiC Interfaces Formed by Dry and Pyrogenic Oxidation. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1341-1344	0.4	2
98	Epitaxial growth of hexagonal and cubic InN films. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 2839-2842	1.3	16

97	Characterization of Carrier Concentration and Mobility in n-type SiC Wafers Using Infrared Reflectance Spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2004</b> , 43, 5151-5156	1.4	20
96	Spectroscopic ellipsometry study on the dielectric functions of GaPN alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 2753-2756		9
95	Improvement in the luminescence efficiency of GaAsN alloys by photoexcitation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 2782-2784		4
94	X-Ray Photoelectron Spectroscopy Studies of Post-Oxidation Process Effects on Oxide/SiC Interfaces. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1033-1036	0.4	4
93	Measurements of the Depth Profile of the Refractive Indices in Oxide Films on SiC by Spectroscopic Ellipsometry. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 800-804	1.4	15
92	Control of Macroscopic Absorption Coefficient of Multicrystalline SiGe by Microscopic Compositional Distribution. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L37-L39	1.4	7
91	Spatial Mapping of the Carrier Concentration and Mobility in SiC Wafers by Micro Fourier-Transform Infrared Spectroscopy. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 621-624	0.4	10
90	Characterization of the Interfaces between SiC and Oxide Films by Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1029-1032	0.4	3
89	Composition analysis of SiO <sub>2</sub> /SiC interfaces by electron spectroscopic measurements using slope-shaped oxide films. <i>Applied Surface Science</i> , <b>2001</b> , 184, 161-166	6.7	98
88	Spectroscopic Ellipsometry Study on the Electronic Structure near the Absorption Edge of GaAsN Alloys. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 228, 269-272	1.3	2
87	Photoluminescence Study on Temperature Dependence of Band Gap Energy of GaAsN Alloys. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 228, 273-277	1.3	27
86	Temperature Dependence of Excitonic $\pi$ -Transition Energies of Ga <sub>x</sub> In <sub>1-x</sub> P Crystals. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 1183-1187	1.4	8
85	Optical characterization of metalorganic vapor-phase epitaxy-grown GaAs <sub>1-x</sub> N <sub>x</sub> alloys using spectroscopic ellipsometry. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 481-484	1.6	10
84	Fabrication and optical properties of GaAs/AlGaAs quantum dot grown in tetrahedral-shaped recesses on GaAs B substrates by MOVPE. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 7, 308-316	3	3
83	Second-Harmonic Generation from GaP/AlP Multilayers on GaP (111) Substrates Based on Quasi-Phase Matching for the Fundamental Standing Wave. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L334-L336	1.4	8
82	Optical Constants of Cubic GaN, AlN, and AlGa <sub>1-x</sub> N <sub>x</sub> Alloys. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L497-L499	1.4	44
81	Characterization of Oxide Films on SiC by Spectroscopic Ellipsometry. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L1054-L1056	1.4	17
80	Quantum Size Effect of Lead Iodide Nanoparticles Formed by a Langmuir-Blodgett Technique. <i>Molecular Crystals and Liquid Crystals</i> , <b>1999</b> , 337, 225-228		1

79	High-Temperature Metalorganic Vapor Phase Epitaxial Growth of GaAs/AlGaAs Quantum Structures in Tetrahedral-Shaped Recesses on GaAs (111)B Substrates. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 459-464	1.4	3
78	Stimulated emission from optically pumped cubic GaN/AlGaIn double heterostructures. <i>Journal of Crystal Growth</i> , <b>1999</b> , 197, 73-77	1.6	9
77	Optical Characterization of Cubic AlGaIn Epilayers by Cathodoluminescence and Spectroscopic Ellipsometry. <i>Physica Status Solidi (B): Basic Research</i> , <b>1999</b> , 216, 211-214	1.3	9
76	Time-Resolved Photoluminescence of Cubic GaN Grown by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , <b>1999</b> , 216, 237-240	1.3	6
75	MOVPE Growth and Luminescence Properties of GaAsN Alloys with Higher Nitrogen Concentrations. <i>Physica Status Solidi A</i> , <b>1999</b> , 176, 231-235		36
74	Substrate Misorientation Dependence of the Hexagonal Phase Inclusion in Cubic GaN Films Grown by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , <b>1999</b> , 176, 513-517		7
73	Selective Growth of Cubic GaN on Patterned GaAs(100) Substrates by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , <b>1999</b> , 176, 557-560		10
72	Arsenic Surfactant and Incorporation Effects on Cubic GaN Grown by Metalorganic Vapor Phase Epitaxy <b>1999</b> ,		2
71	Fabrication of Pb(Zr,Ti)O <sub>3</sub> /MgO/GaN/GaAs structure for optoelectronic device applications. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 227-230	1.6	23
70	Optical transitions in cubic GaN grown on GaAs(1 0 0) substrates by metalorganic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 415-419	1.6	8
69	Investigation of luminescence properties of GaN single crystals grown on 3C-SiC substrates. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 420-424	1.6	10
68	Metalorganic vapor-phase epitaxy of GaP <sub>1-x</sub> As <sub>y</sub> N <sub>x</sub> quaternary alloys on GaP. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 485-489	1.6	7
67	Temperature dependence of photoluminescence of GaP <sub>1-x</sub> N <sub>x</sub> alloys. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 496-499	1.6	11
66	Photoluminescence and photoluminescence-excitation spectroscopy of GaPAsN/GaP lattice-matched multiple quantum well structures. <i>Journal of Crystal Growth</i> , <b>1998</b> , 195, 574-578	1.6	13
65	Theoretical study of conduction band edge formation in GaP <sub>1-x</sub> N <sub>x</sub> alloys using a tight-binding approximation. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 500-504	1.6	5
64	Micro Raman and micro photoluminescence study of cubic GaN grown on 3C-SiC(001) substrates by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>1998</b> , 195, 323-327	1.6	19
63	Exciton diffusion dynamics in quantum nanostructures on V-groove patterned substrates. <i>Superlattices and Microstructures</i> , <b>1998</b> , 23, 395-400	2.8	
62	Characterization of SiGe strained heterostructures grown by molecular beam epitaxy using a Si effusion cell. <i>Thin Solid Films</i> , <b>1998</b> , 321, 241-244	2.2	2



61	A new approach to ZnCdSe quantum dots. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1998</b> , 51, 127-131	3.1	13
60	Molecular beam epitaxy of SiGe heterostructures using a newly designed Si effusion cell. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1998</b> , 51, 170-172	3.1	
59	Self-assembled, very long II-VI semiconductor quantum wires. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1998</b> , 51, 224-228	3.1	3
58	Cleaved cavity stimulated emission from an optically pumped cubic GaN/AlGaIn heterostructure grown on GaAs (100) substrate. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 1931-1933	3.4	14
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53	Sublattice Reversal in GaAs/Si/GaAs (100) Heterostructures by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, L1493-L1496	1.4	32
52	Self Formation and Optical Properties of II-VI Semiconductor Wire Structures. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, L1490-L1493	1.4	2
51	Naturally formed ZnCdSe quantum dots on ZnSe (110) surfaces. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 2413-2415	3.4	52
50	Metalorganic Vapor Phase Epitaxy Growth Features of AlGaAs in Tetrahedral-Shaped Recesses on GaAs (111)B Substrates. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4102-4106	1.4	8
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46	MOVPE Growth of GaPAsN Quaternary Alloys Lattice-Matched to GaP. <i>Materials Research Society Symposia Proceedings</i> , <b>1997</b> , 482, 259		3
45	Photoluminescence properties of cubic GaN grown on GaAs(100) substrates by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 2067-2069	3.4	71
44	Electronic structure of strained-layer quantum wells. <i>Surface Science</i> , <b>1997</b> , 387, 371-382	1.8	3

43	Nitrogen concentration dependence of photoluminescence decay time in GaP <sub>1-x</sub> N <sub>x</sub> alloys. <i>Solid-State Electronics</i> , <b>1997</b> , 41, 231-233	1.7	20
42	Photoluminescence excitation spectroscopy of GaP <sub>1-x</sub> N <sub>x</sub> alloys: conduction-band-edge formation by nitrogen incorporation. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 353-356	1.6	47
41	A highly luminescent crescent-shaped tensile-strained quantum wire laser structure. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 585-589	1.6	9
40	The optical processes in AlInP/GaInP/AlInP quantum wells. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 4592-4598	1.5	20
39	Anomalous optical absorption in ZnCdSe/ZnSe single quantum wells. <i>Solid State Communications</i> , <b>1996</b> , 99, 897-900	1.6	1
38	Growth temperature dependence of AlGaAs spontaneous vertical quantum wells on V-grooved substrates by low-pressure metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>1996</b> , 158, 205-209	1.6	5
37	Time-resolved photoluminescence study on Al <sub>x</sub> Ga <sub>1-x</sub> As spontaneous vertical quantum well structures. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 3221-3223	3.4	1
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35	Optical property of GaAsP/AlGaAs strained-layer quantum well grown on GaAs-(111)B substrate. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 186-188	3.4	3
34	Tensile-strained GaAsP/AlGaAs quantum wells grown by low-pressure metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 3517-3519	2.5	5
33	Composition profile of an AlGaAs epilayer on a V-grooved substrate grown by low-pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 959-961	3.4	12
32	Formation of Cubic GaN on (111)B GaAs by Metal-Organic Vapor-Phase Epitaxy with Dimethylhydrazine. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, 3415-3416	1.4	11
31	Selective Growth of Cubic GaN in Small Areas on Patterned GaAs(100) Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, 694-697	1.4	18
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29	Characterization of Ge/SiGe strained-barrier quantum-well structures using photoreflectance spectroscopy. <i>Physical Review B</i> , <b>1994</b> , 49, 7394-7399	3.3	23
28	Photoluminescence study of (111)-oriented GaAs/GaAsP strained-layer quantum well structure. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 1555-1557	3.4	4
27	Valence-subband level crossing in GaAs/GaAsP strained-barrier quantum well structures observed by circularly polarized photoluminescence excitation spectroscopy. <i>Solid-State Electronics</i> , <b>1994</b> , 37, 915-918	1.7	18
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25	Surface orientation dependence of growth rate of cubic GaN. <i>Journal of Crystal Growth</i> , <b>1994</b> , 145, 197-202	1.6	5
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